

## SWITCHING DIODE

### FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

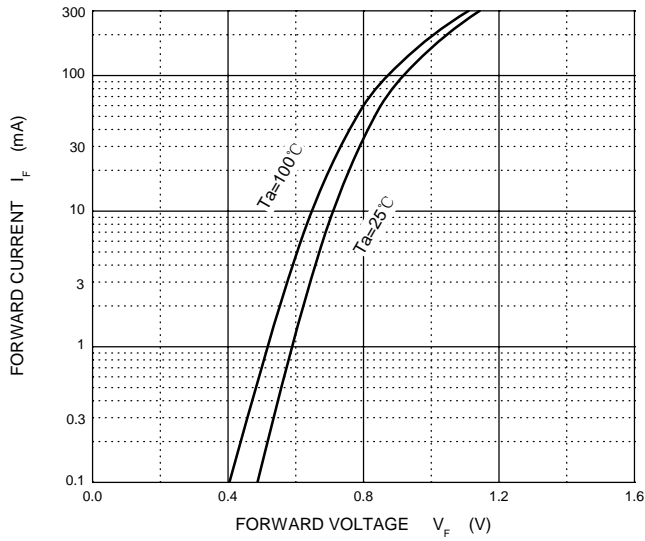
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$	75	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Output Current	$I_O$	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	$I_{FSM}$	2.0	A
Power Dissipation	$P_d$	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

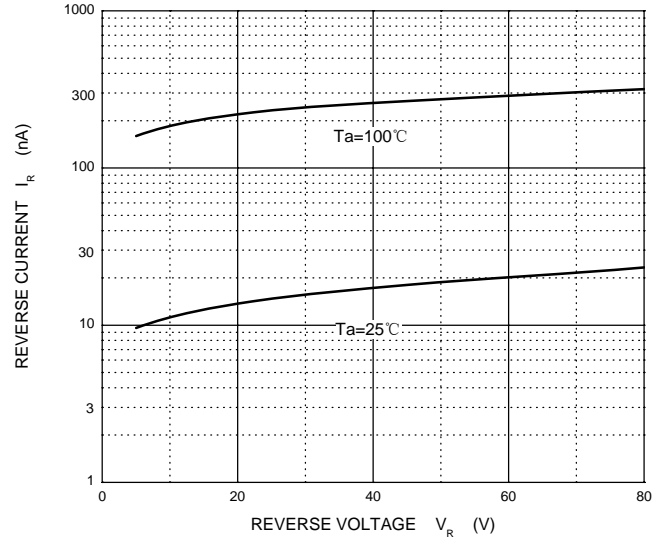
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	75		V
Reverse voltage leakage current	$I_R$	$V_R = 75V$		1	$\mu A$
Forward voltage	$V_F$	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		0.715 0.855 1 1.25	V
Diode capacitance	$C_D$	$V_R = 0, f = 1MHz$		2	pF
Revers recovery time	$t_{rr}$	$I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R,$ $R_L = 100\Omega$		6	ns

## Typical Characteristics

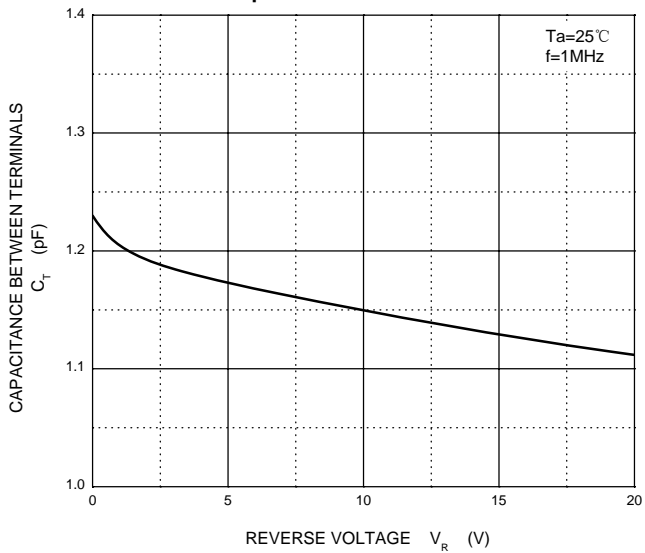
### Forward Characteristics



### Reverse Characteristics



### Capacitance Characteristics



### Power Derating Curve

